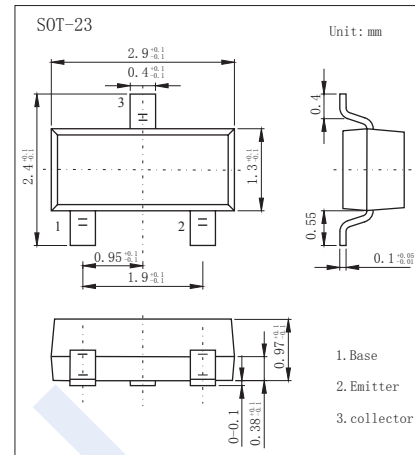


NPN Transistors

BCX70 (KCX70)

■ Features

- Low current (max. 100 mA)
- Low voltage (max. 45 V).
- PNP complements: BCX71 series.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	45	V
Collector - Emitter Voltage	V_{CE0}	45	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_C	100	mA
Peak Collector Current	I_{CM}	200	
Peak Base Current	I_{BM}	200	
Collector Power Dissipation	P_C	250	mW
Thermal Resistance From Junction to Ambient (note.1)	R_{thja}	50	K/W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: Transistor mounted on an FR4 printed-circuit board.

NPN Transistors

BCX70 (KCX70)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = 100 μA, I _E = 0	45			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 1 mA, I _B = 0	45			
Emitter - base breakdown voltage	V _{EBO}	I _E = 100 μA, I _C = 0	5			
Collector-base cut-off current	I _{CBO}	V _{CB} = 45 V, I _E = 0			20	nA
		V _{CB} = 45 V, I _E = 0, T _{amb} = 150°C			20	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 4V, I _C =0			20	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10 mA, I _B =0.25mA	50		350	mV
		I _C =50 mA, I _B =1.25mA	100		550	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =10 mA, I _B =0.25mA	600		850	
		I _C =50 mA, I _B =1.25mA	700		1050	
Base - emitter voltage	V _{BE}	V _{CE} = 5V, I _C = 10μA		520		
		V _{CE} = 5V, I _C = 2mA	550	650	750	
		V _{CE} = 1V, I _C = 50mA		780		
DC current gain	BCX70G BCX70H BCX70J BCX70K	V _{CE} = 5V, I _C = 10μA	-		-	
			40			
			30			
			100			
DC current gain	BCX70G BCX70H BCX70J BCX70K	V _{CE} = 5V, I _C = 2mA	120		220	
			180		310	
			250		460	
			380		630	
DC current gain	BCX70G BCX70H BCX70J BCX70K	V _{CE} = 1V, I _C = 50mA	50			
			70			
			90			
			100			
Collector capacitance	C _c	V _{CB} = 10V, I _E =I _C =0, f=1MHz		1.7		pF
Emitter capacitance	C _e	V _{EB} = 0.5V, I _C =I _C =0, f=1MHz		11		
Noise figure	NF	I _C = 200 μA; V _{CE} = 5 V; R _s = 2 kΩ; f = 1 kHz; B = 200 Hz		2	6	dB
Transition frequency	f _T	V _{CE} = 5V, I _C = 10mA, f=100MHz	100	250		MHz

■ Classification of h_{FE}(2)

Type	BCX70G	BCX70H	BCX70J	BCX70K
Range	120-220	180-310	250-460	380-630
Marking	AG*	AH*	AJ*	AK*